

MC34064, MC33064, NCV33064

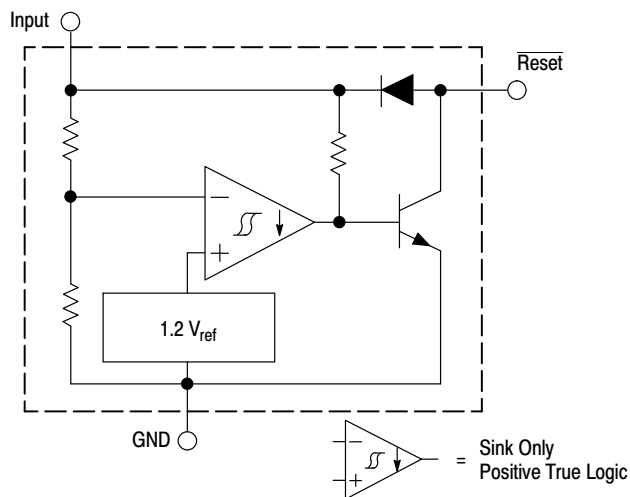
Undervoltage Sensing Circuit

The MC34064 is an undervoltage sensing circuit specifically designed for use as a reset controller in microprocessor-based systems. It offers the designer an economical solution for low voltage detection with a single external resistor. The MC34064 features a trimmed-in-package bandgap reference, and a comparator with precise thresholds and built-in hysteresis to prevent erratic reset operation. The open collector reset output is capable of sinking in excess of 10 mA, and operation is guaranteed down to 1.0 V input with low standby current. The MC devices are packaged in 3-pin TO-92, micro size TSOP-5, 8-pin SOIC-8 and Micro8™ surface mount packages. The NCV device is packaged in SOIC-8 and TO-92.

Applications include direct monitoring of the 5.0 V MPU/logic power supply used in appliance, automotive, consumer and industrial equipment.

Features

- Trimmed-In-Package Temperature Compensated Reference
- Comparator Threshold of 4.6 V at 25°C
- Precise Comparator Thresholds Guaranteed Over Temperature
- Comparator Hysteresis Prevents Erratic Reset
- Reset Output Capable of Sinking in Excess of 10 mA
- Internal Clamp Diode for Discharging Delay Capacitor
- Guaranteed Reset Operation with 1.0 V Input
- Low Standby Current
- Economical TO-92, TSOP-5, SOIC-8 and Micro8 Surface Mount Packages
- NCV Prefix for Automotive and Other Applications Requiring Site and Control Changes
- These Devices are Pb-Free and are RoHS Compliant



This device contains 21 active transistors.

Figure 1. Representative Block Diagram

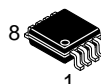


ON Semiconductor®

www.onsemi.com



**SOIC-8
D SUFFIX
CASE 751**

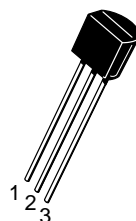


**Micro8
DM SUFFIX
CASE 846A**

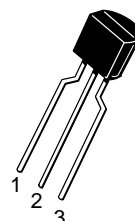


**TSOP-5
SN SUFFIX
CASE 483**

Pin 1. Ground
2. Input
3. Reset
4. NC
5. NC



**STRAIGHT LEAD
BULK PACK**

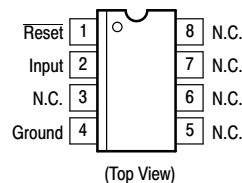


**BENT LEAD
TAPE & REEL
AMMO PACK**

**TO-92
P SUFFIX
CASE 29**

Pin 1. $\overline{\text{Reset}}$
2. Input
3. Ground

PIN CONNECTIONS



ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

DEVICE MARKING INFORMATION

See general marking information in the device marking section on page 7 of this data sheet.

MC34064, MC33064, NCV33064

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Power Input Supply Voltage	V_{in}	-1.0 to 10	V
Reset Output Voltage	V_O	10	V
Reset Output Sink Current (Note 2)	I_{Sink}	Internally Limited	mA
Clamp Diode Forward Current, Reset to Input Pin (Note 2)	I_F	100	mA
Power Dissipation and Thermal Characteristics			
P Suffix, Plastic Package			
Maximum Power Dissipation @ $T_A = 25^\circ\text{C}$	P_D	625	mW
Thermal Resistance, Junction-to-Air	$R_{\theta JA}$	200	$^\circ\text{C/W}$
D Suffix, Plastic Package			
Maximum Power Dissipation @ $T_A = 25^\circ\text{C}$	P_D	625	mW
Thermal Resistance, Junction-to-Air	$R_{\theta JA}$	200	$^\circ\text{C/W}$
DM Suffix, Plastic Package			
Maximum Power Dissipation @ $T_A = 25^\circ\text{C}$	P_D	520	mW
Thermal Resistance, Junction-to-Air	$R_{\theta JA}$	240	$^\circ\text{C/W}$
Operating Junction Temperature	T_J	+150	$^\circ\text{C}$
Operating Ambient Temperature	T_A		$^\circ\text{C}$
MC34064		0 to +70	
MC33064		-40 to +85	
NCV33064		-40 to +125	
Storage Temperature Range	T_{stg}	-65 to +150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- ESD data available upon request.

ELECTRICAL CHARACTERISTICS (For typical values $T_A = 25^\circ\text{C}$, for min/max values T_A is the operating ambient temperature range that applies [Notes 3 and 4] unless otherwise noted.)

Characteristics	Symbol	Min	Typ	Max	Unit
COMPARATOR					
Threshold Voltage					V
High State Output (V_{in} Increasing)	V_{IH}	4.5	4.61	4.7	
Low State Output (V_{in} Decreasing)	V_{IL}	4.5	4.59	4.7	
Hysteresis	V_H	0.01	0.02	0.05	

RESET OUTPUT

Output Sink Saturation	V_{OL}				V
($V_{in} = 4.0\text{ V}$, $I_{Sink} = 8.0\text{ mA}$)		-	0.46	1.0	
($V_{in} = 4.0\text{ V}$, $I_{Sink} = 2.0\text{ mA}$)		-	0.15	0.4	
($V_{in} = 1.0\text{ V}$, $I_{Sink} = 0.1\text{ mA}$)		-	-	0.1	
Output Sink Current (V_{in} , $\overline{\text{Reset}} = 4.0\text{ V}$)	I_{Sink}	10	27	60	mA
Output Off-State Leakage (V_{in} , $\overline{\text{Reset}} = 5.0\text{ V}$)	I_{OH}	-	0.02	0.5	μA
Clamp Diode Forward Voltage, Reset to Input Pin ($I_F = 10\text{ mA}$)	V_F	0.6	0.9	1.2	V

TOTAL DEVICE

Operating Input Voltage Range	V_{in}	1.0 to 6.5	-	-	V
Quiescent Input Current ($V_{in} = 5.0\text{ V}$)	I_{in}	-	390	500	μA

- Maximum package power dissipation limits must be observed.
- Low duty cycle pulse techniques are used during test to maintain junction temperature as close to ambient as possible.
- $T_{low} = 0^\circ\text{C}$ for MC34064 $T_{high} = +70^\circ\text{C}$ for MC34064
 -40°C for MC33064 $+85^\circ\text{C}$ for MC33064
 -40°C for NCV33064 $+125^\circ\text{C}$ for NCV33064
- NCV prefix is for automotive and other applications requiring site and change control.

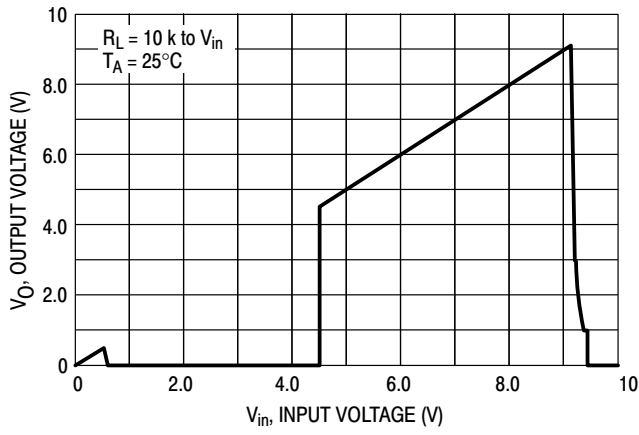


Figure 2. Reset Output Voltage versus Input Voltage

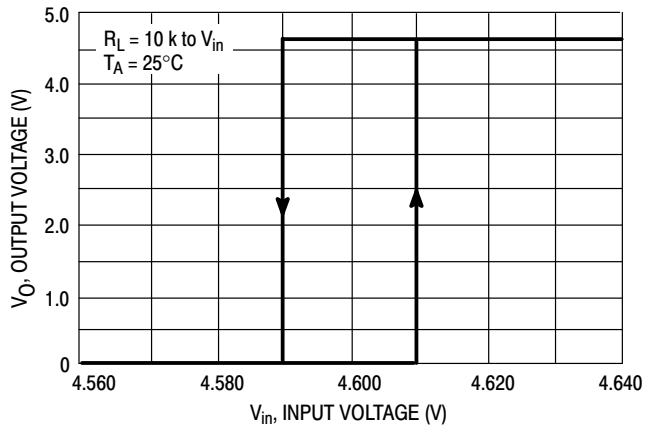


Figure 3. Reset Output Voltage versus Input Voltage

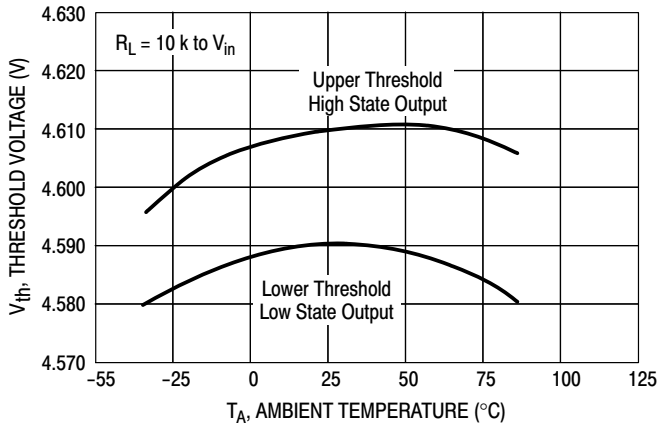


Figure 4. Comparator Threshold Voltage versus Temperature

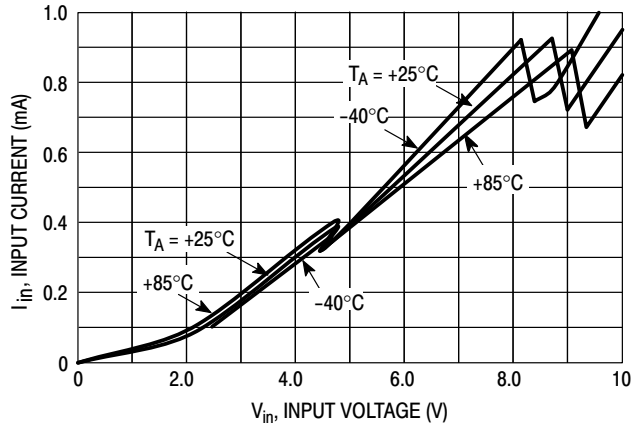


Figure 5. Input Current versus Input Voltage

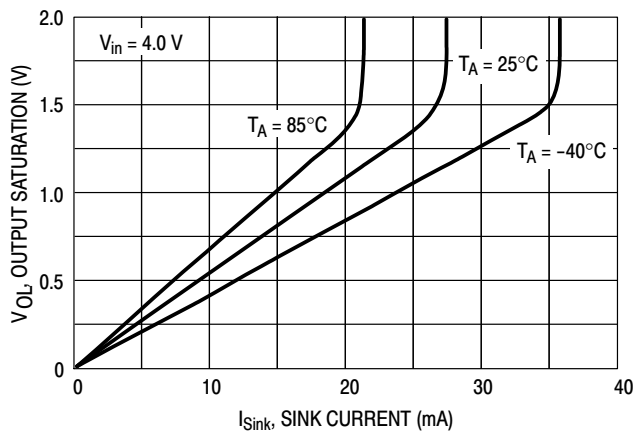


Figure 6. Reset Output Saturation versus Sink Current

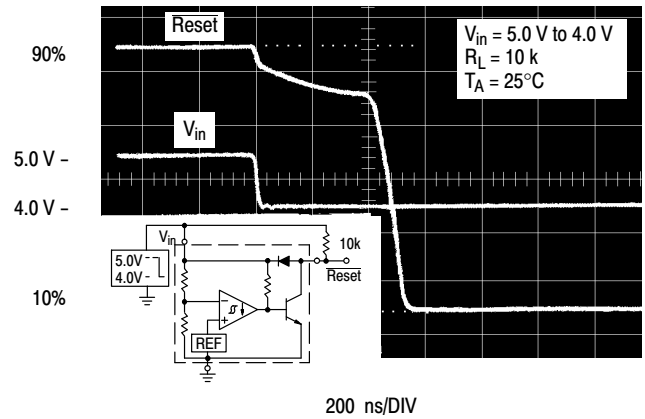


Figure 7. Reset Delay Time

MC34064, MC33064, NCV33064

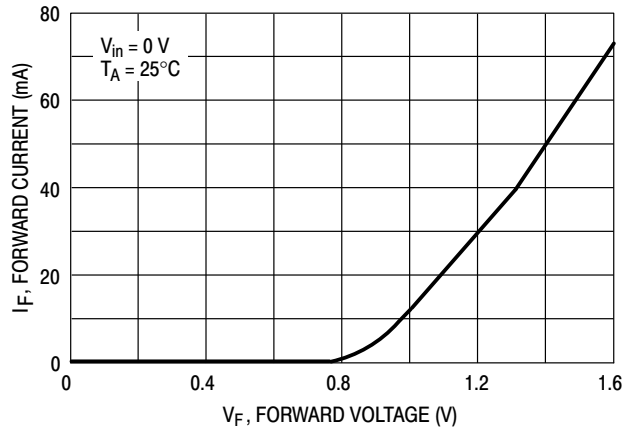


Figure 8. Clamp Diode Forward Current versus Voltage

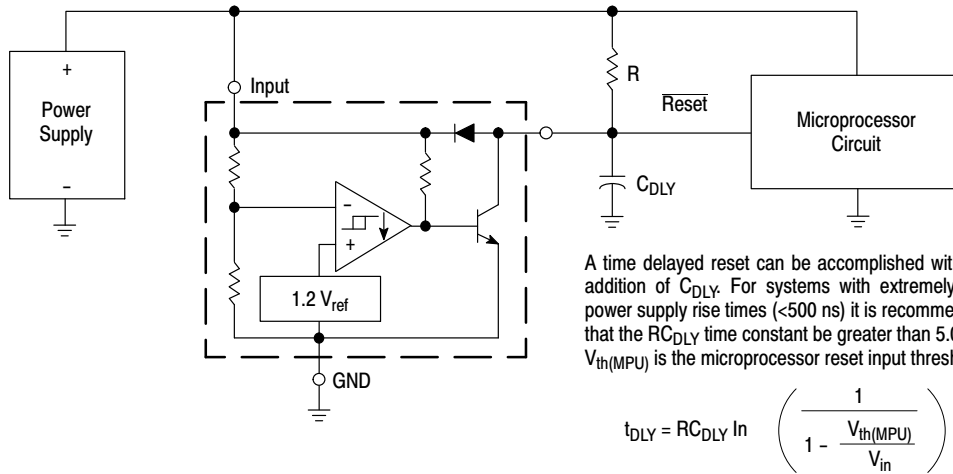
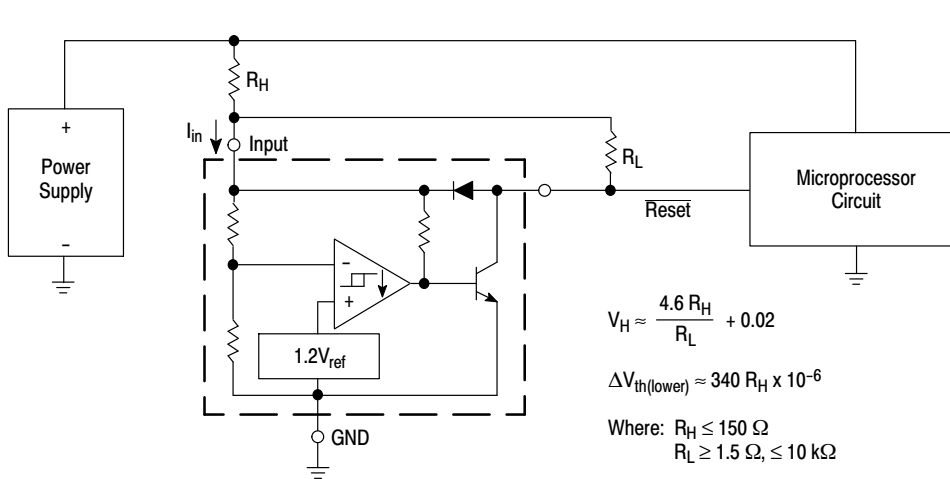


Figure 9. Low Voltage Microprocessor Reset



TEST DATA

V_H (mV)	ΔV_{th} (mV)	R_H (Ω)	R_L (k Ω)
20	0	0	0
51	3.4	10	1.5
40	6.8	20	4.7
81	6.8	20	1.5
71	10	30	2.7
112	10	30	1.5
100	16	47	2.7
164	16	47	1.5
190	34	100	2.7
327	34	100	1.5
276	51	150	2.7
480	51	150	1.5

Comparator hysteresis can be increased with the addition of resistor R_H . The hysteresis equation has been simplified and does not account for the change of input current I_{in} as V_{CC} crosses the comparator threshold (Figure 4). An increase of the lower threshold $\Delta V_{th(lower)}$ will be observed due to I_{in} which is typically $340 \mu A$ at $4.59 V$. The equations are accurate to $\pm 10\%$ with R_H less than 150Ω and R_L between $1.5 k\Omega$ and $10 k\Omega$.

Figure 10. Low Voltage Microprocessor Reset with Additional Hysteresis

MC34064, MC33064, NCV33064

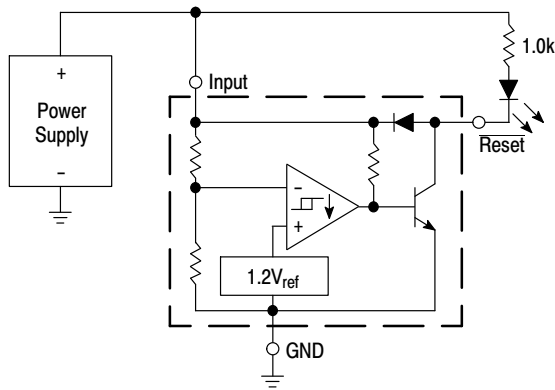


Figure 11. Voltage Monitor

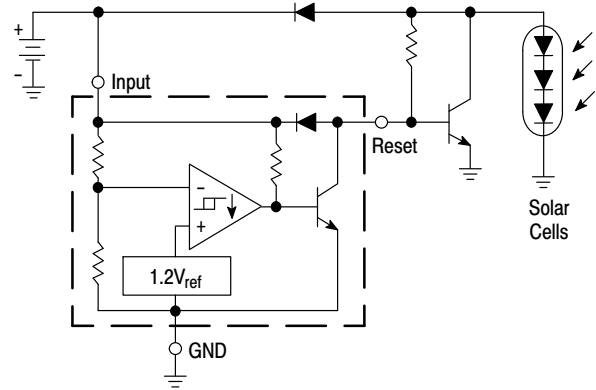
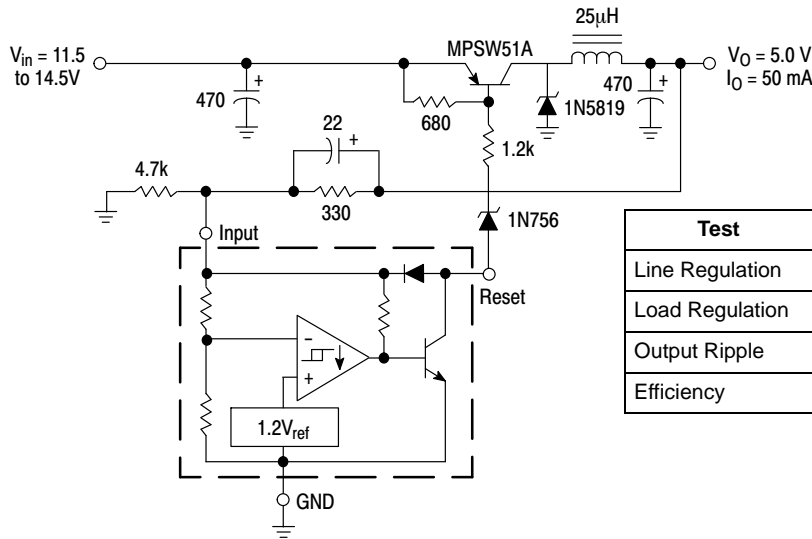
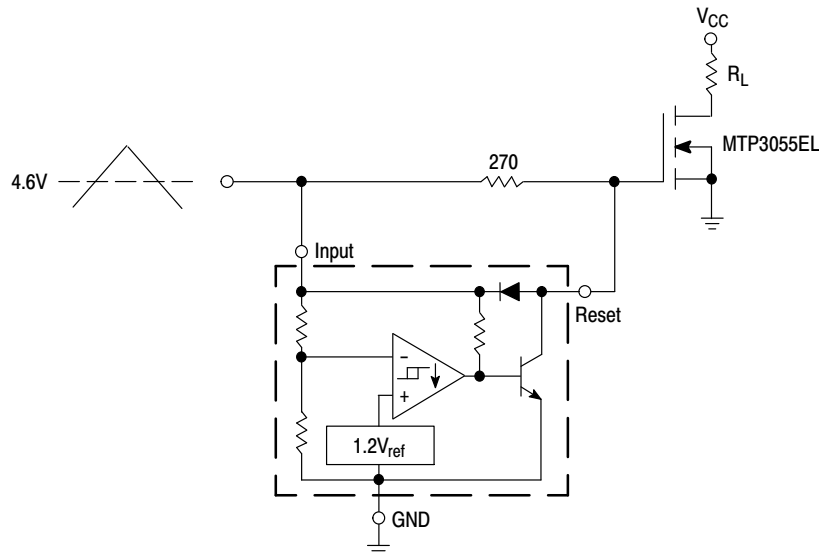


Figure 12. Solar Powered Battery Charger



Test	Conditions	Results
Line Regulation	$V_{in} = 11.5 \text{ V to } 14.5 \text{ V}, I_O = 50 \text{ mA}$	35 mV
Load Regulation	$V_{in} = 12.6 \text{ V}, I_O = 0 \text{ mA to } 50 \text{ mA}$	12 mV
Output Ripple	$V_{in} = 12.6 \text{ V}, I_O = 50 \text{ mA}$	60 mVpp
Efficiency	$V_{in} = 12.6 \text{ V}, I_O = 50 \text{ mA}$	77%

Figure 13. Low Power Switching Regulator



Overheating of the logic level power MOSFET due to insufficient gate voltage can be prevented with the above circuit. When the input signal is below the 4.6 V threshold of the MC34064, its output grounds the gate of the L² MOSFET.

Figure 14. MOSFET Low Voltage Gate Drive Protection

MC34064, MC33064, NCV33064

ORDERING INFORMATION

Device	Operating Temperature Range	Package	Shipping [†]
MC34064D-5G	$T_A = 0^\circ\text{C to } +70^\circ\text{C}$	SOIC-8 (Pb-Free)	98 Units / Rail
MC34064D-5R2G		SOIC-8 (Pb-Free)	2500 Units/ Tape & Reel
MC34064DM-5R2G		Micro8 (Pb-Free)	4000 Units / Tape & Reel
MC34064P-5G		TO-92 (Pb-Free)	2000 Units / Bag
MC34064P-5RAG		TO-92 (Pb-Free)	2000 Units / Tape & Reel
MC34064P-5RPG		TO-92 (Pb-Free)	2000 Units / Ammo Pack
MC34064P-5RMG		TO-92 (Pb-Free)	
MC34064SN-5T1G		TSOP-5 (Pb-Free)	3000 Units / Tape & Reel
MC33064D-5G	$T_A = -40^\circ\text{C to } +85^\circ\text{C}$	SOIC-8 (Pb-Free)	98 Units / Rail
MC33064D-5R2G		SOIC-8 (Pb-Free)	2500 Units / Tape & Reel
MC33064DM-5R2G		Micro8 (Pb-Free)	4000 Units / Tape & Reel
MC33064P-5G		TO-92 (Pb-Free)	2000 Units / Bag
MC33064P-5RAG		TO-92 (Pb-Free)	2000 Units / Tape & Reel
MC33064P-5RPG		TO-92 (Pb-Free)	2000 Units / Ammo Pack
MC33064SN-5T1G		TSOP-5 (Pb-Free)	3000 Units / Tape & Reel
NCV33064D-5R2G*	$T_A = -40^\circ\text{C to } +125^\circ\text{C}$	SOIC-8 (Pb-Free)	2500 Units / Tape & Reel
NCV33064P-5RAG*		TO-92 (Pb-Free)	2000 Units / Tape & Reel
NCV33064P-5RPG*		TO-92 (Pb-Free)	2000 Units / Ammo Pack
NCV33064DM-5R2G*		Micro8 (Pb-Free)	4000 Units / Tape & Reel

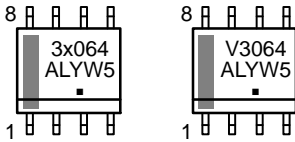
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*NCV33064: $T_{low} = -40^\circ\text{C}$, $T_{high} = +125^\circ\text{C}$. Guaranteed by design. NCV prefix is for automotive and other applications requiring site and change control.

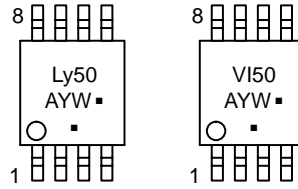
MC34064, MC33064, NCV33064

MARKING DIAGRAMS

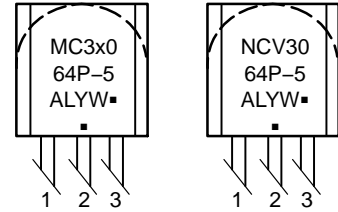
SOIC-8
D SUFFIX
CASE 751



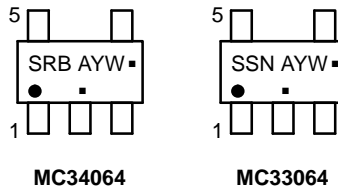
Micro8
DM SUFFIX
CASE 846A



TO-92
P SUFFIX
CASE 29



TSOP-5
SN SUFFIX
CASE 483



- x = 3 or 4
- y = C or I
- A = Assembly Location
- L = Wafer Lot
- Y = Year
- W = Work Week
- = Pb-Free Package

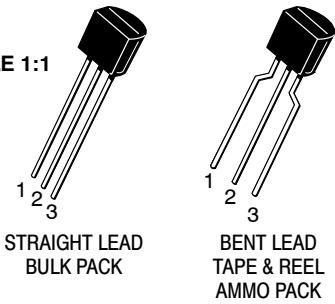
(Note: Microdot may be in either location)

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

ON Semiconductor®

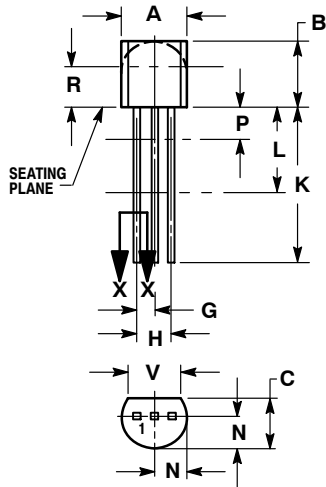


SCALE 1:1

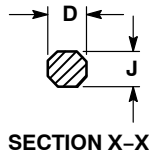


TO-92 (TO-226)
CASE 29-11
ISSUE AM

DATE 09 MAR 2007



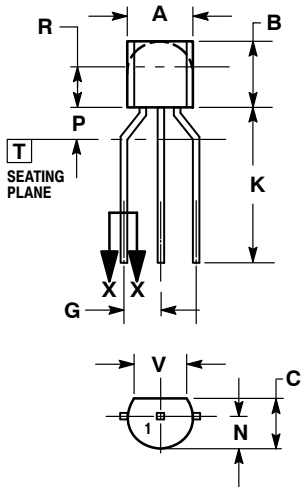
STRAIGHT LEAD
BULK PACK



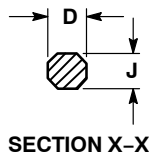
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.115	---	2.93	---
V	0.135	---	3.43	---



BENT LEAD
TAPE & REEL
AMMO PACK



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	MILLIMETERS	
	MIN	MAX
A	4.45	5.20
B	4.32	5.33
C	3.18	4.19
D	0.40	0.54
G	2.40	2.80
J	0.39	0.50
K	12.70	---
N	2.04	2.66
P	1.50	4.00
R	2.93	---
V	3.43	---

STYLES ON PAGE 2

DOCUMENT NUMBER:	98ASB42022B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
STATUS:	ON SEMICONDUCTOR STANDARD	
NEW STANDARD:		
DESCRIPTION:	TO-92 (TO-226)	PAGE 1 OF 3

TO-92 (TO-226)
CASE 29-11
ISSUE AM

DATE 09 MAR 2007

STYLE 1:
 PIN 1. EMITTER
 2. BASE
 3. COLLECTOR

STYLE 2:
 PIN 1. BASE
 2. EMITTER
 3. COLLECTOR

STYLE 3:
 PIN 1. ANODE
 2. ANODE
 3. CATHODE

STYLE 4:
 PIN 1. CATHODE
 2. CATHODE
 3. ANODE

STYLE 5:
 PIN 1. DRAIN
 2. SOURCE
 3. GATE

STYLE 6:
 PIN 1. GATE
 2. SOURCE & SUBSTRATE
 3. DRAIN

STYLE 7:
 PIN 1. SOURCE
 2. DRAIN
 3. GATE

STYLE 8:
 PIN 1. DRAIN
 2. GATE
 3. SOURCE & SUBSTRATE

STYLE 9:
 PIN 1. BASE 1
 2. EMITTER
 3. BASE 2

STYLE 10:
 PIN 1. CATHODE
 2. GATE
 3. ANODE

STYLE 11:
 PIN 1. ANODE
 2. CATHODE & ANODE
 3. CATHODE

STYLE 12:
 PIN 1. MAIN TERMINAL 1
 2. GATE
 3. MAIN TERMINAL 2

STYLE 13:
 PIN 1. ANODE 1
 2. GATE
 3. CATHODE 2

STYLE 14:
 PIN 1. EMITTER
 2. COLLECTOR
 3. BASE

STYLE 15:
 PIN 1. ANODE 1
 2. CATHODE
 3. ANODE 2

STYLE 16:
 PIN 1. ANODE
 2. GATE
 3. CATHODE

STYLE 17:
 PIN 1. COLLECTOR
 2. BASE
 3. EMITTER

STYLE 18:
 PIN 1. ANODE
 2. CATHODE
 3. NOT CONNECTED

STYLE 19:
 PIN 1. GATE
 2. ANODE
 3. CATHODE

STYLE 20:
 PIN 1. NOT CONNECTED
 2. CATHODE
 3. ANODE

STYLE 21:
 PIN 1. COLLECTOR
 2. EMITTER
 3. BASE

STYLE 22:
 PIN 1. SOURCE
 2. GATE
 3. DRAIN

STYLE 23:
 PIN 1. GATE
 2. SOURCE
 3. DRAIN

STYLE 24:
 PIN 1. EMITTER
 2. COLLECTOR/ANODE
 3. CATHODE

STYLE 25:
 PIN 1. MT 1
 2. GATE
 3. MT 2

STYLE 26:
 PIN 1. V_{CC}
 2. GROUND 2
 3. OUTPUT

STYLE 27:
 PIN 1. MT
 2. SUBSTRATE
 3. MT

STYLE 28:
 PIN 1. CATHODE
 2. ANODE
 3. GATE

STYLE 29:
 PIN 1. NOT CONNECTED
 2. ANODE
 3. CATHODE

STYLE 30:
 PIN 1. DRAIN
 2. GATE
 3. SOURCE

STYLE 31:
 PIN 1. GATE
 2. DRAIN
 3. SOURCE

STYLE 32:
 PIN 1. BASE
 2. COLLECTOR
 3. EMITTER

STYLE 33:
 PIN 1. RETURN
 2. INPUT
 3. OUTPUT

STYLE 34:
 PIN 1. INPUT
 2. GROUND
 3. LOGIC

STYLE 35:
 PIN 1. GATE
 2. COLLECTOR
 3. EMITTER

DOCUMENT NUMBER:	98ASB42022B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
STATUS:	ON SEMICONDUCTOR STANDARD	
NEW STANDARD:		
DESCRIPTION:	TO-92 (TO-226)	PAGE 2 OF 3

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

ON Semiconductor®



SCALE 2:1

TSOP-5 CASE 483 ISSUE N

DATE 12 AUG 2020



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. DIMENSION A.
5. OPTIONAL CONSTRUCTION: AN ADDITIONAL TRIMMED LEAD IS ALLOWED IN THIS LOCATION. TRIMMED LEAD NOT TO EXTEND MORE THAN 0.2 FROM BODY.

DIM	MILLIMETERS	
	MIN	MAX
A	2.85	3.15
B	1.35	1.65
C	0.90	1.10
D	0.25	0.50
G	0.95 BSC	
H	0.01	0.10
J	0.10	0.26
K	0.20	0.60
M	0°	10°
S	2.50	3.00

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



- XXX = Specific Device Code
 A = Assembly Location
 Y = Year
 W = Work Week
 ■ = Pb-Free Package
- XXX = Specific Device Code
 M = Date Code
 ■ = Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present.

DOCUMENT NUMBER:	98ARB18753C	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	TSOP-5	PAGE 1 OF 1

ON Semiconductor and ON are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

ON Semiconductor®



SCALE 1:1

SOIC-8 NB
CASE 751-07
ISSUE AK

DATE 16 FEB 2011



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
 5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
 6. 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.80	5.00	0.189	0.197
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
H	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0°	8°	0°	8°
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXXXXX = Specific Device Code
 A = Assembly Location
 L = Wafer Lot
 Y = Year
 W = Work Week
 ■ = Pb-Free Package

XXXXXX = Specific Device Code
 A = Assembly Location
 Y = Year
 WW = Work Week
 ■ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

DOCUMENT NUMBER:	98ASB42564B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	SOIC-8 NB	PAGE 1 OF 2

ON Semiconductor and ON are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

SOIC-8 NB
CASE 751-07
ISSUE AK

DATE 16 FEB 2011

- | | | | |
|--|---|---|---|
| <p>STYLE 1:
 PIN 1. EMITTER
 2. COLLECTOR
 3. COLLECTOR
 4. EMITTER
 5. EMITTER
 6. BASE
 7. BASE
 8. EMITTER</p> | <p>STYLE 2:
 PIN 1. COLLECTOR, DIE, #1
 2. COLLECTOR, #1
 3. COLLECTOR, #2
 4. COLLECTOR, #2
 5. BASE, #2
 6. EMITTER, #2
 7. BASE, #1
 8. EMITTER, #1</p> | <p>STYLE 3:
 PIN 1. DRAIN, DIE #1
 2. DRAIN, #1
 3. DRAIN, #2
 4. DRAIN, #2
 5. GATE, #2
 6. SOURCE, #2
 7. GATE, #1
 8. SOURCE, #1</p> | <p>STYLE 4:
 PIN 1. ANODE
 2. ANODE
 3. ANODE
 4. ANODE
 5. ANODE
 6. ANODE
 7. ANODE
 8. COMMON CATHODE</p> |
| <p>STYLE 5:
 PIN 1. DRAIN
 2. DRAIN
 3. DRAIN
 4. DRAIN
 5. GATE
 6. GATE
 7. SOURCE
 8. SOURCE</p> | <p>STYLE 6:
 PIN 1. SOURCE
 2. DRAIN
 3. DRAIN
 4. SOURCE
 5. SOURCE
 6. GATE
 7. GATE
 8. SOURCE</p> | <p>STYLE 7:
 PIN 1. INPUT
 2. EXTERNAL BYPASS
 3. THIRD STAGE SOURCE
 4. GROUND
 5. DRAIN
 6. GATE 3
 7. SECOND STAGE Vd
 8. FIRST STAGE Vd</p> | <p>STYLE 8:
 PIN 1. COLLECTOR, DIE #1
 2. BASE, #1
 3. BASE, #2
 4. COLLECTOR, #2
 5. COLLECTOR, #2
 6. EMITTER, #2
 7. EMITTER, #1
 8. COLLECTOR, #1</p> |
| <p>STYLE 9:
 PIN 1. EMITTER, COMMON
 2. COLLECTOR, DIE #1
 3. COLLECTOR, DIE #2
 4. EMITTER, COMMON
 5. EMITTER, COMMON
 6. BASE, DIE #2
 7. BASE, DIE #1
 8. EMITTER, COMMON</p> | <p>STYLE 10:
 PIN 1. GROUND
 2. BIAS 1
 3. OUTPUT
 4. GROUND
 5. GROUND
 6. BIAS 2
 7. INPUT
 8. GROUND</p> | <p>STYLE 11:
 PIN 1. SOURCE 1
 2. GATE 1
 3. SOURCE 2
 4. GATE 2
 5. DRAIN 2
 6. DRAIN 2
 7. DRAIN 1
 8. DRAIN 1</p> | <p>STYLE 12:
 PIN 1. SOURCE
 2. SOURCE
 3. SOURCE
 4. GATE
 5. DRAIN
 6. DRAIN
 7. DRAIN
 8. DRAIN</p> |
| <p>STYLE 13:
 PIN 1. N.C.
 2. SOURCE
 3. SOURCE
 4. GATE
 5. DRAIN
 6. DRAIN
 7. DRAIN
 8. DRAIN</p> | <p>STYLE 14:
 PIN 1. N-SOURCE
 2. N-GATE
 3. P-SOURCE
 4. P-GATE
 5. P-DRAIN
 6. P-DRAIN
 7. N-DRAIN
 8. N-DRAIN</p> | <p>STYLE 15:
 PIN 1. ANODE 1
 2. ANODE 1
 3. ANODE 1
 4. ANODE 1
 5. CATHODE, COMMON
 6. CATHODE, COMMON
 7. CATHODE, COMMON
 8. CATHODE, COMMON</p> | <p>STYLE 16:
 PIN 1. EMITTER, DIE #1
 2. BASE, DIE #1
 3. EMITTER, DIE #2
 4. BASE, DIE #2
 5. COLLECTOR, DIE #2
 6. COLLECTOR, DIE #2
 7. COLLECTOR, DIE #1
 8. COLLECTOR, DIE #1</p> |
| <p>STYLE 17:
 PIN 1. VCC
 2. V2OUT
 3. V1OUT
 4. TXE
 5. RXE
 6. VEE
 7. GND
 8. ACC</p> | <p>STYLE 18:
 PIN 1. ANODE
 2. ANODE
 3. SOURCE
 4. GATE
 5. DRAIN
 6. DRAIN
 7. CATHODE
 8. CATHODE</p> | <p>STYLE 19:
 PIN 1. SOURCE 1
 2. GATE 1
 3. SOURCE 2
 4. GATE 2
 5. DRAIN 2
 6. MIRROR 2
 7. DRAIN 1
 8. MIRROR 1</p> | <p>STYLE 20:
 PIN 1. SOURCE (N)
 2. GATE (N)
 3. SOURCE (P)
 4. GATE (P)
 5. DRAIN
 6. DRAIN
 7. DRAIN
 8. DRAIN</p> |
| <p>STYLE 21:
 PIN 1. CATHODE 1
 2. CATHODE 2
 3. CATHODE 3
 4. CATHODE 4
 5. CATHODE 5
 6. COMMON ANODE
 7. COMMON ANODE
 8. CATHODE 6</p> | <p>STYLE 22:
 PIN 1. I/O LINE 1
 2. COMMON CATHODE/VCC
 3. COMMON CATHODE/VCC
 4. I/O LINE 3
 5. COMMON ANODE/GND
 6. I/O LINE 4
 7. I/O LINE 5
 8. COMMON ANODE/GND</p> | <p>STYLE 23:
 PIN 1. LINE 1 IN
 2. COMMON ANODE/GND
 3. COMMON ANODE/GND
 4. LINE 2 IN
 5. LINE 2 OUT
 6. COMMON ANODE/GND
 7. COMMON ANODE/GND
 8. LINE 1 OUT</p> | <p>STYLE 24:
 PIN 1. BASE
 2. EMITTER
 3. COLLECTOR/ANODE
 4. COLLECTOR/ANODE
 5. CATHODE
 6. CATHODE
 7. COLLECTOR/ANODE
 8. COLLECTOR/ANODE</p> |
| <p>STYLE 25:
 PIN 1. VIN
 2. N/C
 3. REXT
 4. GND
 5. IOUT
 6. IOUT
 7. IOUT
 8. IOUT</p> | <p>STYLE 26:
 PIN 1. GND
 2. dv/dt
 3. ENABLE
 4. ILIMIT
 5. SOURCE
 6. SOURCE
 7. SOURCE
 8. VCC</p> | <p>STYLE 27:
 PIN 1. ILIMIT
 2. OVLO
 3. UVLO
 4. INPUT+
 5. SOURCE
 6. SOURCE
 7. SOURCE
 8. DRAIN</p> | <p>STYLE 28:
 PIN 1. SW_TO_GND
 2. DASIC OFF
 3. DASIC_SW_DET
 4. GND
 5. V_MON
 6. VBULK
 7. VBULK
 8. VIN</p> |
| <p>STYLE 29:
 PIN 1. BASE, DIE #1
 2. EMITTER, #1
 3. BASE, #2
 4. EMITTER, #2
 5. COLLECTOR, #2
 6. COLLECTOR, #2
 7. COLLECTOR, #1
 8. COLLECTOR, #1</p> | <p>STYLE 30:
 PIN 1. DRAIN 1
 2. DRAIN 1
 3. GATE 2
 4. SOURCE 2
 5. SOURCE 1/DRAIN 2
 6. SOURCE 1/DRAIN 2
 7. SOURCE 1/DRAIN 2
 8. GATE 1</p> | | |

DOCUMENT NUMBER:	98ASB42564B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	SOIC-8 NB	PAGE 2 OF 2

ON Semiconductor and  are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

ON Semiconductor®



SCALE 2:1

Micro8 CASE 846A-02 ISSUE K

DATE 16 JUL 2020

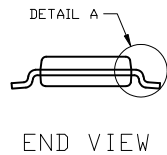


TOP VIEW

NOTE 3



SIDE VIEW



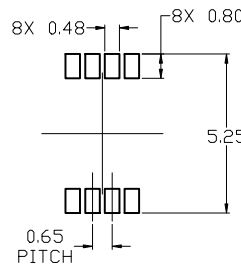
END VIEW

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSION *b* DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.10 mm IN EXCESS OF MAXIMUM MATERIAL CONDITION.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSION OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 mm PER SIDE. DIMENSION E DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 mm PER SIDE. DIMENSIONS D AND E ARE DETERMINED AT DATUM F.
5. DATUMS A AND B ARE TO BE DETERMINED AT DATUM F.
6. A1 IS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.

⌀ 0.08 (0.003) M C B S A S

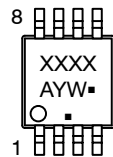
DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	---	---	1.10
A1	0.05	0.08	0.15
<i>b</i>	0.25	0.33	0.40
<i>c</i>	0.13	0.18	0.23
D	2.90	3.00	3.10
E	2.90	3.00	3.10
<i>e</i>	0.65 BSC		
H _E	4.75	4.90	5.05
L	0.40	0.55	0.70



RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERM/D.

GENERIC MARKING DIAGRAM*



- XXXX = Specific Device Code
- A = Assembly Location
- Y = Year
- W = Work Week
- = Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:

1. SOURCE
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN
6. DRAIN
7. DRAIN
8. DRAIN

STYLE 2:

1. SOURCE 1
2. GATE 1
3. SOURCE 2
4. GATE 2
5. DRAIN 2
6. DRAIN 2
7. DRAIN 1
8. DRAIN 1

STYLE 3:

1. N-SOURCE
2. N-GATE
3. P-SOURCE
4. P-GATE
5. P-DRAIN
6. P-DRAIN
7. N-DRAIN
8. N-DRAIN

DOCUMENT NUMBER:	98ASB14087C	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	MICRO8	PAGE 1 OF 1

ON Semiconductor and ON are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

ON Semiconductor and  are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Email Requests to: orderlit@onsemi.com

ON Semiconductor Website: www.onsemi.com

TECHNICAL SUPPORT

North American Technical Support:
Voice Mail: 1 800-282-9855 Toll Free USA/Canada
Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative